

# Fabrication and Application of Carbon Nanotube/Silicon Nanostructures



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The best things in life are beyond money, their price is agony and sweat and devotion...

- Robert A. Heinlein in *Starship Troopers*

The Scientific man does not aim at an immediate result. He does not expect that his advanced ideas will be readily taken up. His work is like that of the planter – for the future. His duty is to lay the foundation for those who are to come, and point the way. He lives and labours and hopes.

- Nikola Tesla

Any sufficiently advanced technology is indistinguishable from magic.

- Arthur C. Clarke

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## Table of contents

|  |              |
|--|--------------|
| <b>Table of contents</b> .....                                       | <b>i</b>     |
| <b>Summary</b> .....   | <b>vii</b>   |
| <b>Declaration</b> .....   | <b>ix</b>    |
| <b>Acknowledgements</b> .....  | <b>xi</b>    |
| <b>List of figures</b> .....   | <b>xiii</b>  |
| <b>List of tables</b> .....  | <b>xxv</b>   |
| <b>Glossary of abbreviations</b> .....                               | <b>xxvii</b> |
| <b>List of publications</b> .....                                    | <b>xxix</b>  |
| <br>   |              |
| <b>Chapter 1</b>   |              |
| <b>Introduction</b> .....  | <b>1</b>     |
| <b>1.1 Overview</b> .....  | <b>2</b>     |
| <b>1.2 Carbon nanotubes</b> .....                                    | <b>5</b>     |
| 1.2.1 History and structure.....                                     | 5            |
| 1.2.2 Properties and applications .....                              | 9            |
| 1.2.3 Synthesis .....  | 12           |
| <b>1.3 Silicon</b> .....   | <b>15</b>    |
| 1.3.1 Bulk silicon.....  | 15           |
| 1.3.2 Porous silicon.....  | 16           |
| <b>1.4 Chemical attachment of carbon nanotubes to surfaces</b> ..... | <b>20</b>    |
| 1.4.1 Carbon nanotube chemistry .....                                | 20           |
| 1.4.2 Carbon nanotube surface attachment.....                        | 20           |
| 1.4.3 Experimental results .....                                     | 22           |
| <b>1.5 Carbon nanotubes for water filtration</b> .....               | <b>25</b>    |
| 1.5.1 Background.....  | 25           |
| 1.5.2 Theoretical studies .....                                      | 26           |
| 1.5.3 Experimental studies.....                                      | 29           |

---

|            |   |           |
|------------|---|-----------|
| <b>1.6</b> | <b>Field emission from carbon nanotubes.....</b>          | <b>35</b> |
| 1.6.1      | Background and theory .....                               | 35        |
| 1.6.2      | Field emission from carbon nanotubes.....                 | 39        |
| <b>1.7</b> | <b>Carbon nanotubes as biointerfacial substrates.....</b> | <b>45</b> |
| 1.7.1      | Background .....  | 45        |
| 1.7.2      | Carbon nanotube biointerfaces .....                       | 45        |
| <b>1.8</b> | <b>Motivation .....</b>                                   | <b>51</b> |
| <b>1.9</b> | <b>References .....</b>                                   | <b>52</b> |

## Chapter 2

|  |  |    |
|--|--|----|
| <b>Experimental details .....</b>                        | <b>65</b>  |    |
| <b>2.1 Carbon nanotubes.....</b>                         | <b>66</b>  |    |
| 2.1.1  | Single-walled carbon nanotubes..... 66                   |    |
| 2.1.2  | Carbon nanotube filtration..... 66                       |    |
| 2.1.3  | Carbon nanotube suspension in dimethyl sulfoxide..... 66 |    |
| 2.1.4  | Double-walled carbon nanotubes .....                     | 67 |
| 2.1.5  | Multi-walled carbon nanotubes .....                      | 67 |
| <b>2.2 Silicon.....</b>                                  | <b>68</b>  |    |
| 2.2.1  | Silicon hydroxylation .....                              | 68 |
| 2.2.2  | APTES monolayer formation on silicon .....               | 68 |
| 2.2.3  | Porous silicon fabrication.....                          | 69 |
| 2.2.4  | APTES monolayer formation on porous silicon .....        | 69 |
| <b>2.3 CNT chemical attachment to silicon.....</b>       | <b>71</b>  |    |
| 2.3.1  | Direct ester attachment of CNTs to Si.....               | 71 |
| 2.3.2  | APTES mediated attachment of CNTs to Si .....            | 72 |
| 2.3.3  | Ester attachment of CNTs to pSi.....                     | 73 |
| 2.3.4  | APTES mediated attachment of CNTs to pSi .....           | 74 |
| 2.3.5  | Patterned attachment of SWCNTs .....                     | 74 |
| <b>2.4 CNT growth by chemical vapour deposition.....</b> | <b>76</b>  |    |
| <b>2.5 Surface characterisation techniques.....</b>      | <b>78</b>  |    |
| 2.5.1  | Atomic force microscopy (AFM).....                       | 78 |

|            |   |           |
|------------|---|-----------|
| 2.5.2      | Scanning electron microscopy (SEM) .....                          | 79        |
| 2.5.3      | Confocal Raman spectroscopy and spectral imaging .....            | 80        |
| 2.5.4      | X-ray photoelectron spectroscopy (XPS) .....                      | 85        |
| 2.5.5      | Fourier transform infrared (FTIR) spectroscopy and microscopy.... | 86        |
| 2.5.6      | Contact angle .....   | 86        |
| <b>2.6</b> | <b>References .....</b>   | <b>88</b> |

## **Chapter 3**

|  |            |
|--|------------|
| <b>Device fabrication .....</b>                              | <b>89</b>  |
| <b>3.1 Introduction .....</b>                                | <b>90</b>  |
| <b>3.2 SWCNT attachment to silicon .....</b>                 | <b>92</b>  |
| 3.2.1 Chemical functionalisation of SWCNTs .....             | 92         |
| 3.2.2 Direct ester attachment of SWCNTs to silicon.....      | 93         |
| 3.2.3 Attachment of SWCNTs to APTES functionalised Si .....  | 99         |
| <b>3.3 SWCNT attachment to pSi .....</b>                     | <b>102</b> |
| 3.3.1 Porous silicon.....                                    | 102        |
| 3.3.2 Direct ester attachment of SWCNTs to pSi.....          | 104        |
| 3.3.3 Attachment of SWCNTs to APTES functionalised pSi ..... | 105        |
| <b>3.4 DWCNT attachment to silicon .....</b>                 | <b>111</b> |
| 3.4.1 Chemical functionalisation of DWCNTs.....              | 111        |
| 3.4.2 Attachment of DWCNTs to silicon .....                  | 112        |
| <b>3.5 MWCNT attachment to silicon.....</b>                  | <b>115</b> |
| 3.5.1 Chemical functionalisation of MWCNTs.....              | 115        |
| 3.5.2 Attachment of MWCNT to silicon .....                   | 116        |
| <b>3.6 CNT growth via chemical vapour deposition.....</b>    | <b>118</b> |
| <b>3.7 Conclusions.....</b>                                  | <b>125</b> |
| <b>3.8 References .....</b>                                  | <b>126</b> |

## **Chapter 4**

|  |            |
|--|------------|
| <b>Controlled carbon nanotube placement.....</b> | <b>131</b> |
| <b>4.1 Introduction .....</b>                    | <b>132</b> |

---

|            |   |            |
|------------|---|------------|
| <b>4.2</b> | <b>Experimental methods .....</b>               | <b>135</b> |
| 4.2.1      | Fabrication of pSi with pore size gradient..... | 135        |
| 4.2.2      | Fabrication of an APTES gradient .....          | 135        |
| <b>4.3</b> | <b>Patterned attachment of SWCNTs .....</b>     | <b>137</b> |
| <b>4.4</b> | <b>SWCNT surface coverage gradients.....</b>    | <b>143</b> |
| 4.4.1      | pSi topographical gradient.....                 | 143        |
| 4.4.2      | APTES chemical gradient .....                   | 148        |
| <b>4.5</b> | <b>Conclusions.....</b>                         | <b>154</b> |
| <b>4.6</b> | <b>References .....</b>                         | <b>155</b> |

## Chapter 5

|   |  |            |
|---|--|------------|
| <b>Mass transport through CNT and pSi membranes .....</b> | <b>159</b>   |            |
| <b>5.1</b>  | <b>Introduction .....</b>  | <b>160</b> |
| <b>5.2</b>  | <b>Experimental details.....</b>   | <b>164</b> |
| 5.2.1   | Fabrication and functionalisation of pSi membranes .....                       | 164        |
| 5.2.2   | Dye transport properties through pSi membranes.....                            | 165        |
| 5.2.3   | Water transport.....   | 166        |
| 5.2.4   | Fabrication of SWCNT membrane.....   | 167        |
| <b>5.3</b>  | <b>Mass transport through pSi.....</b>   | <b>169</b> |
| 5.3.1   | Fabrication and characterisation of pSi membranes.....                         | 169        |
| 5.3.2   | Dye transport and selectivity properties of functionalised pSi membranes ..... | 175        |
| 5.3.3   | Pressure driven water transport through pSi membranes.....                     | 181        |
| <b>5.4</b>  | <b>Mass transport through SWCNT membrane .....</b>                             | <b>183</b> |
| 5.4.1   | Fabrication of SWCNT membrane.....   | 183        |
| 5.4.2   | Water transport through SWCNT membrane.....                                    | 193        |
| <b>5.5</b>  | <b>Conclusions.....</b>  | <b>200</b> |
| <b>5.6</b>  | <b>References .....</b>  | <b>201</b> |

## Chapter 6

|   |            |
|---|------------|
| <b>Field emission from CNT electrodes .....</b> | <b>203</b> |
|---|------------|

---

|            |  |            |
|------------|--|------------|
| <b>6.1</b> | <b>Introduction .....</b>                            | <b>204</b> |
| <b>6.2</b> | <b>Experimental details .....</b>                    | <b>206</b> |
| <b>6.3</b> | <b>Field emission from SWCNTs .....</b>              | <b>208</b> |
| 6.3.1      | Effect of SWCNT attachment time.....                 | 208        |
| 6.3.2      | Field emission from polymer encapsulated SWCNTs..... | 213        |
| <b>6.4</b> | <b>Field emission from DWCNTs and MWCNTs .....</b>   | <b>215</b> |
| <b>6.5</b> | <b>Field emission stability from CNTs.....</b>       | <b>219</b> |
| 6.5.1      | SWCNT field emission stability.....                  | 219        |
| 6.5.2      | DWCNT field emission stability.....                  | 227        |
| 6.5.3      | MWCNT field emission stability.....                  | 229        |
| <b>6.6</b> | <b>Conclusions.....</b>                              | <b>232</b> |
| <b>6.7</b> | <b>References .....</b>                              | <b>233</b> |

## **Chapter 7**

|            |   |            |
|------------|---|------------|
|            | <b>CNTs as biointerfacial substrates.....</b> | <b>235</b> |
| <b>7.1</b> | <b>Introduction .....</b>                     | <b>236</b> |
| <b>7.2</b> | <b>Experimental details .....</b>             | <b>238</b> |
| 7.2.1      | SWCNT biointerface fabrication.....           | 238        |
| 7.2.2      | Cell culture and staining.....                | 238        |
| 7.2.3      | Fluorescence microscopy.....                  | 239        |
| 7.2.4      | Gene transfection by permeabilisation .....   | 240        |
| 7.2.5      | Gene transfection by electroporation.....     | 240        |
| <b>7.3</b> | <b>Cell immobilisation .....</b>              | <b>242</b> |
| 7.3.1      | Cell morphology and proliferation .....       | 242        |
| 7.3.2      | AFM and SEM imaging.....                      | 249        |
| <b>7.4</b> | <b>Gene transfection.....</b>                 | <b>252</b> |
| 7.4.1      | Gene transfection by permeabilisation .....   | 252        |
| 7.4.2      | Gene transfection by electroporation.....     | 261        |
| <b>7.5</b> | <b>Conclusions.....</b>                       | <b>266</b> |
| <b>7.6</b> | <b>References .....</b>                       | <b>267</b> |

---

## Chapter 8

|                                    |            |
|------------------------------------|------------|
| <b>Conclusions .....</b>           | <b>271</b> |
| <b>8.1 Conclusions.....</b>        | <b>272</b> |
| <b>8.2 Future directions .....</b> | <b>274</b> |
| <b>8.3 References .....</b>        | <b>280</b> |



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## Summary

The amazing electrical and mechanical properties of carbon nanotubes (CNTs) make them ideal for use in a variety of applications, many of which require the CNTs to be surface bound. Here the applicability of nanostructures based upon CNTs chemically attached to silicon to the fields of water filtration, field emission and as biomaterial interfaces is investigated.

Initial experiments studied the chemical attachment and alignment of different CNT types to silicon. Single-walled carbon nanotubes (SWCNTs) were found to form vertically aligned arrays on both flat silicon and porous silicon (pSi). Double-walled carbon nanotubes (DWCNTs) were found to exhibit both vertical and random alignment while multi-walled carbon nanotubes (MWCNTs) exhibited an exclusive horizontal orientation. The variation in alignment is attributed to the level of crystallinity and functionalisation of each CNT type as determined by Raman spectroscopy.

The control of the placement of SWCNTs on silicon was further investigated by fabricating both surface coverage gradients and patterns of SWCNTs. Gradients were fabricated following two protocols, both of which produced surfaces which consist of all possible SWCNT coverage's. SWCNT patterns were produced by forming an initial chemical pattern on the silicon surface for subsequent selective SWCNT chemical attachment.

CNT membranes for water filtration were fabricated by chemically attaching SWCNTs to permeable pSi membranes. Gaps between the SWCNTs were filled by spin coating polystyrene onto the surface. The SWCNT tips were revealed by etching the polystyrene matrix via water plasma treatment. The fabricated membranes were found to have a water permeability of  $0.022 \text{ mm}^3 \text{ cm}^{-2} \text{ s}^{-1} \text{ atm}^{-1}$ . Comparisons to commercial nanofiltration membranes and other published CNT membranes are made and improvements to membrane fabrication are discussed.

Field emission experiments were completed for all CNT types chemically attached to silicon. All samples exhibited field emission of electrons with characteristics varying with CNT diameter and vertical alignment. The emission

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stability of each CNT type was investigated with the SWCNTs exhibiting the most stable emission. Comparison of emission characteristics and stability to other CNT field emission substrates are made.

The behaviour of a mammalian neuronal cell line on SWCNTs chemically attached to porous silicon was investigated. Fluorescence microscopy revealed that the cells had a strong affinity for the SWCNT substrate and that the SWCNTs may compromise the cell membrane allowing small fluorescent molecules to enter the nuclear envelope. Experiments to determine if plasmid DNA could be inserted into the cell via the SWCNTs was completed with results indicating the SWCNTs did not promote DNA transfection for the neuronal cell line.

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## Declaration

I certify that this Thesis does not incorporate without acknowledgment any material previously submitted for a degree or diploma in any university; and that to the best of my knowledge and belief it does not contain any material previously published or written by another person except where due reference is made in the text.

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Cameron J. Shearer



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## Acknowledgements

This Thesis would not have been possible without the assistance of many people who I should acknowledge. Chapter 1 contains parts of a review article published in *Advanced Materials*; this work was co-authored with Kristina Constantopoulos, Amanda Ellis, Nico Voelcker and Joe Shapter. The pattern work presented in Chapter 4 was inspired by an original idea of Ben Flavel, Martin Sweetman then came up with a protocol to form silane patterns which I then used for nanotube attachment. The porous silicon membrane dye transport in Chapter 5 was completed by Leonora Velleman, she also analysed and interpreted the data. The pressure driven water transport, also in Chapter 5, was completed at the University of Bath in the laboratory of Davide Mattia with the help of Fernando Acosta. An ARNAM student travel grant assisted in the travel and accommodation costs for that trip. The field emission experiments shown in Chapter 6 were all completed at the University of Newcastle. I would like to thank Paul Dastoor for allowing me to visit on three occasions. The field emission experiments were assisted originally by Kane O'Donnell and Lars Thomsen, and by Adam Fahy and Matthew Barr on the final visit. The field emission work would never have been completed without the influence of Jamie Quinton, and I thank him for making the most enjoyable and successful aspect of my PhD possible. Fran Harding completed most of the cell culture, cell staining and fluorescence microscopy in Chapter 7, the remainder was completed by Qi Peng. The data presented in Chapter 7 was largely championed by Nico Voelcker who urged collaboration between Fran and myself which became a nice side-project to focus upon when other experiments weren't going as hoped.

I have had the privilege to work in the Smart Surface Structures group at Flinders. Despite only having a single fumehood and rarely containing a post-doc we seem to meet or beat the output of any other group. I think this is largely in part to the hard working culture imparted by Matt Nussio and Ben Flavel. Mark, Lachlan, Chris, Kate, Sam, Anders, Adam, Dan, Ash and others I have forgotten have all been fun to work with. I also spent some time in the Voelcker lab, particularly early in my PhD, where I was helped immensely by the pilots in the cockpit: Steve, Martin and Andy J.

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I am lucky to have two families that have helped me throughout these years of study. Both my parents and Lauren's parents have been happy for me to be poor for another few years in the hope that I will eventually get a real job. I am extremely lucky to have Lauren in my life, she has been very supportive and happy to be the bread winner for the past few years. Hopefully I can repay your kindness in the future.

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## List of Figures

- Figure 1.1:** Comparison of (a) top-down and (b) bottom-up approaches toward miniaturisation. In (a), miniature bulls were fabricated following a two-photon polymerisation technique, scale bars, 2  $\mu\text{m}$ . In (b), individual xenon atoms are moved using a scanning tunnelling microscope to form 0.5 nm high letters.....3
- Figure 1.2:** ‘Ball and stick’ representation of (a) single-walled CNT (SWCNT), (b) double-walled CNT (DWCNT) and (c) multi-walled CNT (MWCNT). Images made using Nanotube Modeller ([www.jcrystal.com](http://www.jcrystal.com)). .....6
- Figure 1.3:** (a) Schematic of unrolled SWCNT showing chiral vector  $C$  and how different values of the integers  $n$  and  $m$  affect the electronic property of the SWCNT. (b, c, d) The direction of the chiral vector affects the appearance of the nanotube showing (b) (4,4) armchair shape, (c) (6,0) zig-zag shape and (d) (5, 3) example of a chiral shape.....8
- Figure 1.4:** (a, b, c, d) Band structures in reciprocal space, as calculated by the tight binding method, of (a, b) graphene, (c) metallic (4, 4) SWCNT, (d) semi-conducting (5, 3) SWCNT showing the wave-vectors as yellow lines and the K-points (Fermi-level points) as red dots. The blue dot represents energy maxima and the pink points represent saddle (M) points. (e, f) represent electronic band structures of (e) (4, 4) metallic nanotube where wave vectors cross a K-point and (f) (5, 3) semiconducting nanotube where no wave vectors cross a K-point.....9
- Figure 1.5:** Summary of CNT synthesis methods (a) arc discharge, (c) laser ablation, and (e) chemical vapour deposition along with SEM images (b, d, f) showing the morphology of the CNTs produced. Scale bar in (d) 100 nm. ....13
- Figure 1.6:** Schematic of the band diagrams of (a) n-type and (b) p-type semiconductors under no bias and negative bias. ....16
- Figure 1.7:** (a) Schematic of the etching cell used for the anodic etching of silicon. (b) Top-down SEM of porous silicon showing the irregularly shaped pores produced. ....17
- Figure 1.8:** Porous silicon formation mechanism showing (a) reaction steps and (b) hole migration during pore formation.....18
- Figure 1.9:** Basic reaction scheme of the mechanism of DCC (red) assisted coupling of carboxylic acid functionalised CNTs (molecule 1, black) to amines, alcohols and thiols (molecule 3, blue).(a) The starting carboxylic acid (1) reacts with DCC to form an activated ester (2). (c) This can rearrange to form the stable unwanted by-product N-acylurea (6) or (b) it can undergo nucleophilic attack from the electron rich N, O or S to form a stable amide, ester or thioester linkage to the  $R_2$  group (5). .....21

---

|   |    |
|---|----|
| <b>Figure 1.10:</b> Schematics and published AFM images of SWCNTs chemically attached to (a) gold via a cystamine linkage, (b) silicon via direct ester linkage, and (c) patterned amine terminated silane on silicon. ....   | 23 |
| <b>Figure 1.11:</b> Water occupancy inside a SWCNT (a) structure of hydrogen bonded chain of water molecules within the SWCNT and (b) probability distribution of water binding energies of (red) confined and (blue) bulk water, the coloured arrows indicate average binding energies.....  | 27 |
| <b>Figure 1.12:</b> Schematic of the fabrication process of aligned MWCNT membranes by Hinds <i>et al.</i> ....   | 30 |
| <b>Figure 1.13:</b> Schematic of the DWCNT membrane fabrication of Holt <i>et al.</i> ....  | 32 |
| <b>Figure 1.14:</b> Field emission models showing how the shape of the potential barrier changes for (a) no field (b) an electric field, (c) a larger electric field and (d) when the Coulomb potential is included in the calculation.....   | 36 |
| <b>Figure 1.15:</b> (a) SEM of SWCNT deposited from a paste, (b) J-V curves and (c) emission stability from varying plasma treatments. ....   | 43 |
| <b>Figure 1.16:</b> (a, b, c) SEM images depicting the attachment of cells to a carpet of VA-CNTs. (a) The tips of the VA-CNTs are in intimate contact with the cell surface. (b) The bending and deformation of the tubes is occurring via biomechanical forces. (c) Neuronal cells adhere preferentially to isolated islands of pristine CNTs. (d) Confocal fluorescence image of neurons (red) and glia cells (green) on a large CNT island. Scale bar in (c, d) 10 $\mu\text{m}$ . .... | 46 |
| <b>Figure 1.17:</b> Schematics of electroporation. (a) Cells in suspension or (b) cells immobilised on a surfaces are exposed to an electric field in order to deliver target material. ....  | 49 |
| <b>Figure 1.18:</b> Summary of results of electroporation on MWCNT showing (a) AFM image of randomly oriented MWCNTs on surface ( $5 \times 5 \mu\text{m}^2$ ). Fluorescence microscopy images after electroporation and gene transfection of a green fluorescent plasmid showing (b) control surface without MWCNTs and (c) a MWCNT surface. Green cells in (b, c) indicate gene transfection, images $1.5 \times 1.5 \text{ mm}^2$ .....  | 50 |
| <b>Figure 2.1:</b> Schematic of the porous silicon etching cell.....  | 69 |
| <b>Figure 2.2:</b> Schematic of the direct ester attachment of CNTs to silicon. ....  | 71 |
| <b>Figure 2.3:</b> Schematic of the APTES mediated attachment of CNTs to silicon.....   | 72 |
| <b>Figure 2.4:</b> Schematic of the direct ester CNT attachment to pSi. ....  | 73 |

---



---

|  |    |
|--|----|
| <b>Figure 2.5:</b> Schematic of APTES mediated attachment of CNTs to pSi .....   | 74 |
| <b>Figure 2.6:</b> Schematic of patterned attachment of SWCNTs to silicon.....   | 75 |
| <b>Figure 2.7:</b> Schematic of CNT growth by chemical vapour deposition. ....   | 76 |
| <b>Figure 2.8:</b> Schematic of AFM operation.....   | 78 |
| <b>Figure 2.9:</b> Summary of possible scattering processes.....   | 81 |
| <b>Figure 2.10:</b> (a) Cross sectional view of a SWCNT showing the radial vibration of the RBM, with (b) vibration of D-band, and (c) vibrations of G-band with $G^+$ peak arising from vibrations along the tube axis and $G^-$ peak arising from vibrations around the circumference of the tube..... | 82 |
| <b>Figure 2.11:</b> Schematic of principle set up of Raman microscope. Image modified from supplier.....   | 83 |
| <b>Figure 2.12:</b> Example of how Raman spectral image is created from many individual spectra.....   | 84 |
| <b>Figure 2.13:</b> Example of water contact angle measurement showing (a) original image and (b) after analysis using the Image J plugin DropSnaker where blue dots were manually inserted and red dots were inserted by the software to give output values.....  | 87 |
| <b>Figure 3.1:</b> (a, b) SEM images (XL-30) of (a) pristine SWCNTs as purchased and (b) SWCNTs ‘cut’ for 8 hr, as described in Chapter 2. (c, d) Photographs of SWCNTs dispersed in DMSO after 1 day of incubation. (c) Pristine SWCNTs and (d) cut SWCNTs.....   | 92 |
| <b>Figure 3.2:</b> AFM images of SWCNTs attached to silicon via an ester linkage with varying silicon hydroxylation methods, (a,b) 2-step base-acid method, (c) ozone treated and (d) Piranha treated. AFM images are $5 \times 5 \mu\text{m}^2$ with a z scale of 50 nm.....                            | 95 |
| <b>Figure 3.3:</b> Graphs of (a) normalised SWCNT coverage and (b) average SWCNT bundle diameter vs. SWCNT attachment time, as determined by AFM. Dashed lines added to guide the eye.....   | 96 |
| <b>Figure 3.4:</b> (a) Raman spectral image and (b) Raman spectrum of SWCNTs chemically attached to silicon via ester attachment. Raman spectrum average of 2 x 120 sec accumulation.....  | 98 |
| <b>Figure 3.5:</b> WCA photographs of (a) Piranha treated silicon and (b) APTES modified silicon.....  | 99 |

---

---

|  |     |
|--|-----|
| <b>Figure 3.6:</b> AFM images of SWCNTs attached to silicon via APTES monolayer (a) top down and (b) 3-D. AFM images are $5 \times 5 \mu\text{m}^2$ with a z scale of 50 nm.....   | 100 |
| <b>Figure 3.7:</b> (a) Raman spectral image and (b) Raman spectrum of SWCNTs chemically attached to silicon via an APTES monolayer. Raman spectrum average of $2 \times 120$ sec accumulations.....  | 101 |
| <b>Figure 3.8:</b> AFM image of freshly etched pSi. Etching conditions: 1:1 (v/v) HF/ethanol, 66 mA, 120 sec.....  | 102 |
| <b>Figure 3.9:</b> FTIR spectra of pSi, which has been (a) freshly etched, (b) ozone oxidised (45 min) and (c) wet chemical oxidised (Piranha solution). Spectra in (b) are offset for clarity.....  | 103 |
| <b>Figure 3.10:</b> AFM image of SWCNTs chemically attached to pSi following the direct ester attachment method on Piranha-oxidised pSi.....   | 104 |
| <b>Figure 3.11:</b> Schematic representation of (a) oxidised pSi, (b) oxidised pSi after reaction with a carboxylic acid containing molecule (eg., ‘cut’ SWCNT), (c) oxidised pSi after APTES immobilisation and (d) pSi after APTES immobilisation and carboxylic acid attachment.....  | 105 |
| <b>Figure 3.12:</b> Transmission FTIR spectra of hydroxylated pSi substrates (ozone; 10 min) followed by (a) APTES functionalisation and (b) SWCNT attachment to APTES monolayer (24 hr attachment time). Inset shows zoom of amine peak area ( $3500 \text{ cm}^{-1}$ to $3100 \text{ cm}^{-1}$ ) for the APTES functionalised pSi substrate. Spectra offset for clarity.....                             | 106 |
| <b>Figure 3.13:</b> AFM images of (a) pSi after 5 min of APTES treatment (0 % surface coverage, $5 \times 5 \mu\text{m}^2$ , z scale 50 nm) and SWCNT attachment on APTES functionalised pSi ( $5 \times 5 \mu\text{m}^2$ images, z scale 50 nm) for attachment times of (b) 5 min (18 % coverage), (c) 1 hr (48 % coverage), (d) 24 hr (52 % coverage) and (e) 3D image of (c) after 1 hr attachment..... | 108 |
| <b>Figure 3.14:</b> Change in percentage surface coverage with incubation time of APTES silanised pSi wafer in a SWCNT solution. Dashed line added to guide the eye.....   | 109 |
| <b>Figure 3.15:</b> (a) Raman spectral image of SWCNTs chemically attached to pSi via the APTES attachment method and (b) Raman spectrum of SWCNTs on pSi showing the high background fluorescence of pSi. Spectrum average of $3 \times 60$ sec.....  | 110 |
| <b>Figure 3.16:</b> SEM images (XL-30) of (a) pristine DWCNTs and (b) cut/functionalised DWCNTs and (c) Raman spectrum of pristine DWCNTs with zoom of RBM region (inset). Raman spectrum average of $2 \times 120$ sec accumulations.....   | 112 |

---

|   |     |
|---|-----|
| <b>Figure 3.17:</b> (a) Top down and (b) 3-D AFM as well as (c) Raman spectra of DWCNTs chemically attached to silicon with zoom showing RBM region (inset). Raman spectrum average of 2 x 60 sec accumulations.....  | 114 |
| <b>Figure 3.18:</b> AFM images of (a) ‘cleaned’ MWCNTs and (b) Cut MWCNTs using the ‘3-acid cutting system’ drop-cast onto a silicon wafer. AFM images are 5 x 5 $\mu\text{m}^2$ with a z scale of 50 nm.....   | 115 |
| <b>Figure 3.19:</b> (a, b) AFM images and (c) Raman spectrum of MWCNTs chemically attached to silicon via (a) direct ester attachment and (b, c) APTES mediated attachment. AFM images are 5 x 5 $\mu\text{m}^2$ with a z scale of 50 nm, Raman spectrum is the average of 2 x 120 sec acquisitions.....  | 117 |
| <b>Figure 3.20:</b> SEM images (CamScan) of CNTs grown on silicon via CVD showing (a, b) vertical alignment, (c) zoom of side view of VA-CNTs and (d) randomly oriented CNTs.....   | 118 |
| <b>Figure 3.21:</b> (a) Raman spectral image of CNTs grown on silicon via CVD and (b) Raman spectrum of the CVD grown CNTs. Raman spectrum is the average of 3 x 30 sec acquisitions.....   | 119 |
| <b>Figure 3.22:</b> (a, c) AFM and (b, d) section analysis of 3 nm iron sputtered onto a silicon surface (a, b) fresh and (c, d) after heating to 750 °C under pre-CNT growth conditions.....   | 121 |
| <b>Figure 3.23:</b> (a, c) AFM and (b, d) section analysis of (a, b) silicon surface with 10 nm of aluminium and 3 nm of iron after heating to 750 °C under pre-CNT growth conditions and (c, d) silicon surface with 10 nm of Al sputtered.....  | 122 |
| <b>Figure 3.24:</b> Plot showing recorded temperature within tube furnace for varying input temperatures from 750 °C (red series) to 680 °C (green series) and 650 °C (blue series).....  | 124 |
| <b>Figure 4.1:</b> Schematic illustrating the fabrication process of SWCNT patterns and gradients. (a) APTES patterning via photolithography to produce a SWCNT gradient, (b) a topographical gradient created by the asymmetric anodisation of silicon and (c) a chemical gradient created by vapour phase diffusion of APTES onto oxidised silicon..... | 134 |
| <b>Figure 4.2:</b> Etching cell configurations for the fabrication of ‘normal’ (left) and gradient (right) pSi.....   | 135 |
| <b>Figure 4.3:</b> Schematic of the apparatus used for APTES gradient fabrication (top view).....   | 136 |
| <b>Figure 4.4:</b> SEM images of photoresist patterns on silicon showing various shapes and sizes of patterns.....  | 137 |

|  |     |
|--|-----|
| <b>Figure 4.5:</b> IR mapping of APTES pattern on pSi showing (a, b) spectra of points (a) within and (b) outside of pattern (insets) with insets showing peaks of interest in more detail, (c) IR spectral map obtained by mapping peak height at $1505\text{ cm}^{-1}$ (indicated by * in (a, b) with (d) optical image of area and (e) overlay of spectral map over optical image. .... | 139 |
| <b>Figure 4.6:</b> Raman spectral images of SWCNT patterns on silicon. (a, b) half-half surface patterns with (a) bare silicon side and (b) Si-APTES-SWCNT side. (c) Optical microscope image of area of investigation for attachment of (c, d) SWCNTs to patterned APTES on silicon. ....   | 141 |
| <b>Figure 4.7:</b> (a) Photograph of gradient pSi film indicating the three regions: (region 1) closest to electrode, (region 2) middle region and (region 3) furthest from the electrode. (b) Tapping mode AFM images showing pore size decreasing with distance from the Pt electrode. Scale bars = 500 nm. ....   | 143 |
| <b>Figure 4.8:</b> Tapping mode AFM height images of SWCNTs attached to gradient pSi surfaces etched at (a) 40 mA (b) 50 mA, (c) 55 mA and (d) 60 mA showing (i) region 1, (ii) region 2 and (iii) region 3. Scale bars = $1\text{ }\mu\text{m}$ . ....  | 146 |
| <b>Figure 4.9:</b> Plots showing SWCNT coverage as a function of (a) the average and (b) the maximum pore size of the pSi surface. ....  | 147 |
| <b>Figure 4.10:</b> (a) Digital photographs and (b) WCA values of water droplets deposited at increasing distance (from 5 – 30 mm at 5 mm intervals) from the APTES-filled reservoir. ....   | 148 |
| <b>Figure 4.11:</b> Raman spectral images of G-band peak intensity at different distances from the APTES-filled reservoir on the SWCNT-decorated gradient. Scale bar = $4\text{ }\mu\text{m}$ . ....   | 149 |
| <b>Figure 4.12:</b> Change in average Raman G-band peak intensity with distance from APTES-filled reservoir after SWCNT covalent attachment without backfill. ....   | 150 |
| <b>Figure 4.13:</b> Raman spectral images of G-band peak intensity of SWCNTs immobilised on APTES gradient after PTMS backfilling of silicon wafer at increasing distances from the APTES-filled reservoir. Scale bar $4 = \mu\text{m}$ . ....   | 152 |
| <b>Figure 4.14:</b> (a) Change in average Raman G-band peak intensity with distance from APTES-filled reservoir after SWCNT covalent attachment with PTMS backfill (inset) zoom of area from 15 to 20 mm. (b) Plot of average G-band peak intensity vs. WCA. The dashed line serves as a guide to the eye. ....  | 153 |
| <b>Figure 5.1:</b> Comparison of CNT membrane fabrication procedures followed by (a) Hinds <i>et al.</i> and (b) Holt <i>et al.</i> Detail of fabrication given in Section 1.5.3. ....   | 161 |
| <b>Figure 5.2:</b> Schematic of the assembly of a SWCNT membrane supported on a pSi substrate. ....  | 163 |

|   |     |
|---|-----|
| <b>Figure 5.3:</b> Schematic of the chemical modification of pSi membranes with (a) the hydrophobic fluorinated silane (PFDS), (b) the hydrophilic silane (PEGS) and (c) APTES for SWCNT attachment. ....   | 165 |
| <b>Figure 5.4:</b> (a, b) Schematic of U-tube configuration used for dye diffusion experiments with the pSi membrane separating the feed and permeate cells. (a) initial configuration with solvent only in the permeate cell and (b) after experiment completed with dye in permeate cell. Structure of the two dyes investigated (c) the hydrophobic dye Rubpy and (d) the hydrophilic Rose Bengal (RB). .... | 166 |
| <b>Figure 5.5:</b> Schematic of pressure driven water transport apparatus. ....   | 167 |
| <b>Figure 5.6:</b> Photographs of pSi membranes (a) attached to the silicon wafer and (b) lifted off the silicon wafer. ....  | 169 |
| <b>Figure 5.7:</b> SEM images of (a) top and (b) bottom of pSi membrane, (c, d) side views of entire layer (c) and zoom of edge, and (e) pore size distribution graph from the top layer of pSi. Images (a, b, d) from the NanoLab SEM while (c) was from the CamScan. ....   | 171 |
| <b>Figure 5.8:</b> XPS analysis of silanes on pSi membranes (red series) pSi-PFDS and (black series) pSi-PEGS. ....   | 173 |
| <b>Figure 5.9:</b> High resolution XPS spectra of the C 1s peak from (red series) pSi-PFDS and (black series) pSi-PEGS. ....  | 174 |
| <b>Figure 5.10:</b> FTIR spectra of pSi (blue series) ozone oxidised, (red series) pSi-PFDS and (black series) pSi-PEGS. ....   | 175 |
| <b>Figure 5.11:</b> Transport of a hydrophobic (Rubpy, green series) and hydrophilic (RB, purple series) dye through pSi membranes. Where (a) is an unfunctionalised membrane, (b) is a hydrophobic (PFDS) functionalised membrane and (c) is a hydrophilic (PEGS) functionalised membrane. ....  | 176 |
| <b>Figure 5.12:</b> Dye transport experiments of (I) Rubpy and (II) RB through (a) unfunctionalised pSi, (b) hydrophobic pSi-PFDS and (c) hydrophilic pSi-PEGS at three different initial dye concentrations. ....  | 177 |
| <b>Figure 5.13:</b> Pressure driven water transport through (blue series) unfunctionalised and (red series) PFDS (hydrophobic) functionalised pSi at a constant applied pressure (inset). ....  | 182 |
| <b>Figure 5.14:</b> Top down (a, c, e) and 3-D (b, d, f) AFM images of SWCNTs on pSi membrane surfaces. Figures (a, b) depict a pSi membrane surface after 1 hr of SWCNT attachment, (c, d) is the same surface after sonication in acetone to remove physisorbed SWCNTs, and (e, f) is a different pSi membrane after 2 hr of SWCNT attachment and sonication in acetone. ....                                 | 185 |

---

|   |     |
|---|-----|
| <b>Figure 5.15:</b> (I) AFM (II) AFM cross sectional analysis and (III) 10 x optical microscope images of polystyrene films spun onto silicon with increasing water plasma etching time: (a) 0 min, (b) 1 min, (c) 2 min, and (d) 3 min. ....   | 187 |
| <b>Figure 5.16:</b> (I) Aerial AFM image (5 x 5 μm, z scale 50 nm), (II) 3-D AFM image, (III) AFM image of scratched cross and (IV) cross section analysis of polystyrene spun onto VA-SWCNTs on pSi surfaces including (a) before water plasma exposure, (b) after 1 min of water plasma exposure and (c) after 2 min of water plasma exposure. .... | 189 |
| <b>Figure 5.17:</b> (I) Optical microscope, (II) aerial (5 x 5 μm, z scale 50 nm) and (III) 3-D AFM images of different areas (a, b, c, and d) of the same sample prepared by chemically attaching SWCNTs to a permeable pSi membrane and depositing a thin film of polystyrene. ....   | 191 |
| <b>Figure 5.18:</b> Schematic of effect of substrate on polymer deposition. (a) pSi film supported on Si substrate leads to even thin polymer film while for (b) the pSi membrane the vacuum can affect the polymer resulting in a inhomogeneous polymer film. ....   | 192 |
| <b>Figure 5.19:</b> (a) Aerial AFM (5 x 5 μm, z scale 50 nm), (b) optical microscope image, and (c) 3-D AFM image of PS thin film deposited by the ‘spin-drop’ method onto a pSi membrane-SWCNT substrate. ....   | 193 |
| <b>Figure 5.20:</b> Schematic of SWCNT membranes prepared. (a) bare pSi membrane with PS thin film deposited and pSi membrane with attached VA-SWCNTs with PS deposited before (b) and after (c) water plasma exposure. ....  | 194 |
| <b>Figure 5.21:</b> Summary of pressure driven water flow through pSi-PS sample showing (a) mass of water transported and (b) applied pressure vs. time. ....   | 195 |
| <b>Figure 5.22:</b> Summary of water flow through pSi-SWCNT-PS (1 min water plasma) showing (a) raw data of mass of water collected (b) applied pressure (c) zoom of area from 2.1 to 3.4 hr, and (d) scale drift removed data vs. time. ....   | 196 |
| <b>Figure 6.1:</b> Schematic of prepared samples for field emission studies. ....   | 205 |
| <b>Figure 6.2:</b> Field emission system at the University of Newcastle showing (a) ultra-high vacuum chamber, (b) power supply and picoammeter, (c) sample stage configuration and (d) schematic of field emission experimental apparatus. ....  | 206 |
| <b>Figure 6.3:</b> Field emission sweeps for SWCNT chemically anchored to n-type silicon for varying SWCNT attachment times with (inset) Fowler-Nordheim plots. ....  | 208 |
| <b>Figure 6.4:</b> Graphs of effect of SWCNT attachment time on (a) electric field enhancement factor ( $\beta$ ) and (b) the turn-on voltage ( $E_{to}$ ). ....  | 210 |

---

|  |     |
|--|-----|
| <b>Figure 6.5:</b> J-F curve attempting to achieve maximum current output for Si-SWCNT surface. Maximum wattage output of power supply reached before maximum current from sample.....   | 212 |
| <b>Figure 6.6:</b> FE sweeps for SWCNT surfaces with varying thickness of polystyrene.....   | 214 |
| <b>Figure 6.7:</b> (a, b, c) Aerial and (d, e, f) 3-D AFM images of (a, d) SWCNTs, (b, e) DWCNTs and (c, f) MWCNTs chemically attached to silicon. White circles in (b) indicate laying down DWCNTs while black circles indicated VA-DWCNTs.....   | 215 |
| <b>Figure 6.8:</b> Summary of field emission (I) J-F sweeps and (II) F-N plots for different CNT types chemically attached to silicon showing (a) low current and (b) high current sweeps. ....  | 217 |
| <b>Figure 6.9:</b> A 60 hr FE stability test of a Si-SWCNT surface with a constant current of $10 \mu\text{A}$ ( $\sim 10 \mu\text{A cm}^{-2}$ ).....  | 220 |
| <b>Figure 6.10:</b> A 60 min FE stability test of FE from a Si-SWCNT surface at a current density of $\sim 110 \mu\text{A cm}^{-2}$ .....  | 221 |
| <b>Figure 6.11:</b> A 15 hr FE stability test of a Si-SWCNT surface at a constant current density output of $780 \mu\text{A cm}^{-2}$ .....  | 223 |
| <b>Figure 6.12:</b> FE stability of a Si-SWCNT surface coated with a thin film of PS. ....   | 225 |
| <b>Figure 6.13:</b> Consecutive FE stability experiments from Si-SWCNT-polystyrene electrodes showing the change in time for the roll-off behaviour to occur. ....   | 226 |
| <b>Figure 6.14:</b> FE stability of a DWCNT electrode at $80 \mu\text{A cm}^{-2}$ over 70 min.....   | 227 |
| <b>Figure 6.15:</b> FE stability of a Si-DWCNT electrode at $\sim 80 \mu\text{A cm}^{-2}$ over 15 hr.....  | 228 |
| <b>Figure 6.16:</b> FE stability of a Si-MWCNT electrode at $10 \mu\text{A cm}^{-2}$ for 45 min.....   | 230 |
| <b>Figure 7.1:</b> Schematic detailing the preparation of (a) a SWCNT-decorated pSi substrate surface and (b) a patterned pSi-SWCNT substrate surface and the resulting attachment of neuroblastoma cells (SK-N-SH). Both preparation schemes involve the chemical attachment of SWCNTs to an amino silane (APTES) on pSi via carbodiimide (DCC) assisted coupling. .... | 237 |
| <b>Figure 7.2:</b> Schematic of the electroporation apparatus.....   | 241 |
| <b>Figure 7.3:</b> Fluorescence microscopy images of phalloidin stained SK-N-SH neuroblastoma cells immobilised on (a, d) oxidised pSi, (b, e) APTES-functionalised pSi and (c, f) SWCNT-decorated pSi. Scale bars (a – c) = $100 \mu\text{m}$ , (d – f) $50 \mu\text{m}$ . ....   | 243 |



|   |     |
|---|-----|
| <b>Figure 7.4:</b> Fluorescence microscopy images of cytoplasm stained SK-N-SH neuroblastoma cells using CMRA. (a) pSi control, (b) 1 min of SWCNT attachment (low density) and (c) 2 hr of SWCNT attachment (high density). Scale bar 50 $\mu\text{m}$ .....   | 244 |
| <b>Figure 7.5:</b> Fluorescence microscopy image of membrane stained SK-N-SH neuroblastoma cells using DIOC <sub>18</sub> (3) on (a, c) oxidised pSi and (b, d) SWCNT-decorated pSi surfaces at different magnifications. Arrows added in (d) to highlight examples of dark spots observed in membrane. Scale bar 50 $\mu\text{m}$ .....                  | 245 |
| <b>Figure 7.6:</b> Fluorescence microscopy images of SK-N-SH neuroblastoma cells stained with (a, b) propidium iodide (PI) and (c, d) fluorescein diacetate (FDA) on (a, c) oxidised pSi and (b, d) SWCNT-decorated pSi substrates. Scale bar 50 $\mu\text{m}$ .....  | 246 |
| <b>Figure 7.7:</b> Fluorescence microscopy images of SK-N-SH neuroblastoma cells stained with (a) propidium iodide (PI) and (b) fluorescein diacetate (FDA) on a SWCNT-decorated pSi substrates after 48 hr of cell culture. Scale bar 50 $\mu\text{m}$ .....   | 247 |
| <b>Figure 7.8:</b> Fluorescence microscopy images of SK-N-SH neuroblastoma cells stained with CellTracker Orange showing preferential attachment to SWCNT-decorated patterns on a pSi substrate showing (a) circle and (b) line pattern. The regions in between those decorated with nanotubes were PEG functionalised. Scale bar 100 $\mu\text{m}$ ..... | 248 |
| <b>Figure 7.9:</b> Summary of SEM images of SK-N-SH on pSi-SWCNT substrates showing cell culture and spreading of lamellipodia (NanoLab SEM).....   | 249 |
| <b>Figure 7.10:</b> AFM image of edge of a SK-N-SH cell on a pSi-SWCNT substrate. ....  | 250 |
| <b>Figure 7.11:</b> I pDNA fluorescence and II Hoechst staining + pDNA of SK-N-SH cells on (a) pSi, (b) pSi-APTES and (c) pSi-APTES-SWCNT substrates after the gene transfection experiment.....  | 253 |
| <b>Figure 7.12:</b> I pDNA fluorescence and II Hoechst staining + pDNA of SK-N-SH cells on (a) pSi, (b) pSi-APTES and (c) pSi-APTES-SWCNT substrates after gene transfection experiment with Effectene added. ....  | 254 |
| <b>Figure 7.13:</b> I pDNA fluorescence and II Hoechst + pDNA staining of SK-N-SH cells on (a) flat Si, (b) flat Si-APTES and (c) flat Si-APTES-SWCNT substrates after gene transfection experiment with Effectene added.....   | 256 |
| <b>Figure 7.14:</b> Schematic of SWCNTs chemically attached to Si substrates with positively charged diethylenetriamine (DETA) electrostatically binding pDNA to the substrate prior to cell culture. ....  | 257 |
| <b>Figure 7.15:</b> XPS analysis to determine if the amine containing diethylenetriamine (DETA) is bound to the surface after SWCNT attachment via (a, c) direct ester  |     |



---

attachment and (b, d) APTES mediated attachment showing (a, b) survey scans and (c, d) higher resolution spectra of the N 1s peak. ....259

**Figure 7.16:** I pDNA fluorescence and II Hoechst + pDNA staining of SK-N-SH cells on (a) Si-SWCNT, (b) Si-SWCNT-DETA, (c) Si-APTES-SWCNT and (d) Si-APTES-SWCNT-DETA substrates after gene transfection experiment with Effectene added.....260

**Figure 7.17:** Summary of initial electroporation experiments showing fluorescence microscope images of SK-N-SH cells stained with both Hoechst and pDNA on (a) Si-SWCNT, (b) Si-SWCNT + Effectene and (c) Si + Effectene.....262

**Figure 7.18:** Fluorescence microscope images of electroporation of SK-N-SH cells on Si-SWCNT-DETA substrates at varying applied voltages showing (I) pDNA expressing GFP and (II) Hoechst stain. ....264

**Figure 8.1:** Publication number for articles containing both “carbon nanotube” and “field emission” obtained using SciFinder search function 8/8/11.....276

**Figure 8.2:** Proposed schematic of the chemical attachment of DNA to carboxy-CNTs via a cleavable linker containing a disulphide group. ....277

**Figure 8.3:** Schematic of proposed improved electroporation apparatus where both cell culture and electroporation are completed within the same cell. ....278



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## List of Tables

|  |     |
|--|-----|
| <b>Table 1.1:</b> Characteristics and applications of pressure driven membrane technologies.....   | 26  |
| <b>Table 1.2:</b> Summary of water molecule transport, ion conductance and study of desalination potential of CNT membranes.....   | 28  |
| <b>Table 1.3:</b> Pressure driven flow through MWCNT membranes.....  | 31  |
| <b>Table 1.4:</b> Comparisons of the gas and water flow enhancements (over their respective theoretical models) for 3 DWCNT membranes and a commercial polycarbonate membrane..... | 33  |
| <b>Table 1.5:</b> Summary of field emission properties from carbon nanotubes.....  | 40  |
| <b>Table 3.1:</b> Raman peak position and assignment for SWCNTs on silicon.....  | 98  |
| <b>Table 3.2:</b> RBM peak positions and corresponding calculated diameter for DWCNTs.....   | 112 |
| <b>Table 4.1:</b> AFM pore size analysis of the pore size gradients produced by different applied currents.....  | 144 |
| <b>Table 4.2:</b> Summary of percentage SWCNT coverage on each region of the gradient pSi etched at different etching currents.....  | 145 |
| <b>Table 5.1:</b> Advancing contact angle measurements for the unfunctionalised, PFDS functionalised and PEGS functionalised pSi membranes.....                                    | 172 |
| <b>Table 5.2:</b> Flux and permeability data for Rubpy and RB transport through unfunctionalised, PFDS-functionalised and PEGS-functionalised pSi membranes.....                   | 178 |
| <b>Table 5.3:</b> Effect of water plasma exposure time on polystyrene thin film thickness.....   | 188 |
| <b>Table 5.4:</b> Comparison of membrane permeability between experimental and theoretical carbon nanotube membranes.....  | 197 |
| <b>Table 5.5:</b> Permeability values for commercial polyamide thin film composite nanofiltration and reverse osmosis membranes.....   | 199 |
| <b>Table 6.1:</b> Summary of field emission characteristics of Si-SWCNT surfaces with varying polystyrene film thickness.....  | 214 |

---

|  |     |
|--|-----|
| <b>Table 6.2:</b> Summary of FE characteristics of SWCNTs, DWCNTs and MWCNTs chemically attached to silicon.....                         | 218 |
| <b>Table 7.1:</b> Summary of WCA and cell area measurements of neuronal cells on the three surfaces used as cell culture substrates..... | 243 |
| <b>Table 7.2:</b> Summary of transfection efficiencies for pDNA with Effectene on the pSi based substrates.....                          | 254 |
| <b>Table 7.3:</b> Summary of transfection efficiencies for pDNA with Effectene on the flat Si based substrates.....                      | 256 |
| <b>Table 7.4:</b> Summary of transfection efficiencies adsorbed pDNA with Effectene on SWCNT substrates. ....                            | 261 |

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## Glossary of abbreviations

| Abbreviation           | Definition                                 |
|------------------------|--|
| AFM                    | atomic force microscopy                    |
| APTES                  | 3-aminopropyl triethoxysilane              |
| b                      | electric field enhancement factor          |
| CMRA                   | CellTracker orange cytoplasm stain         |
| CNT                    | carbon nanotube                            |
| CTA                    | chain transfer agent                       |
| CVD                    | chemical vapour deposition                 |
| D-band                 | disorder Band                              |
| DCC                    | dicyclohexyl carbodiimide                  |
| DETA                   | Diethylenetriamine                         |
| DIOC <sub>18</sub> (3) | green fluorescent cell membrane stain      |
| DMEM                   | Dulbecco's modified eagle medium           |
| DMF                    | dimethyl formamide                         |
| DMSO                   | dimethyl Sulfoxide                         |
| DNA                    | deoxyribosenucleic acid                    |
| dPBS                   | Dulbecco's phosphate buffered saline       |
| DWCNT                  | double-walled carbon nanotube              |
| E <sub>F</sub>         | Fermi energy                               |
| E <sub>to</sub>        | turn-on voltage                            |
| FDA                    | fluorescein diacetate                      |
| FE                     | field emission                             |
| FET                    | field effect transistor                    |
| F-N                    | Fowler-Nordheim                            |
| FTIR                   | fourier transform infrared                 |
| G-band                 | graphene band                              |
| GFP                    | green fluorescent protein                  |
| GO                     | graphene oxide                             |
| HEK                    | human embryonic kidney                     |
| HF                     | hydrofluoric acid                          |
| ITO                    | indium tin oxide                           |
| LCD                    | liquid crystal display                     |
| MD                     | molecular dynamics                         |
| MWCNT                  | multi-walled carbon nanotube               |
| pAl                    | porous alumina                             |
| pDNA                   | plasmid DNA                                |
| PECVD                  | plasma-enhanced chemical vapour deposition |

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| <b>Abbreviation</b> | <b>Definition</b>                             |
|---------------------|---|
| PEGS                | polyethylene glycol silane                    |
| PEI                 | poly(ethylimine)                              |
| PFDS                | Fluorinated silane                            |
| PI                  | propidium iodide                              |
| PMMA                | poly(methylmethacrylate)                      |
| PS                  | poly(styrene)                                 |
| pSi                 | porous silicon                                |
| PTFE                | poly(tetrafluoroethylene)                     |
| PTMS                | propyl trimethoxysilane                       |
| RAFT                | reverse addition fragmentation chain transfer |
| RB                  | rose bengal                                   |
| RBM                 | radial creathing mode                         |
| RNA                 | ribosenucleic acid                            |
| RO                  | reverse Osmosis                               |
| Rubpy               | ruthenium based dye                           |
| SA                  | self assembly                                 |
| SAM                 | self assembled Monolayer                      |
| SEM                 | Scanning Electron Microscopy                  |
| Si                  | Silicon                                       |
| SK-N-SH             | mammalian neuroblastoma cell line             |
| STM                 | scanning tunnelling microscope                |
| SWCNT               | single-walled carbon nanotube                 |
| TEM                 | transmission electron microscopy              |
| VA                  | vertically aligned                            |
| WCA                 | water contact angle                           |
| XPS                 | X-ray photoelectron spectroscopy              |

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Parts of the above publications have been reproduced in this Thesis as follows:

- Chapter 1 contains parts of [5]
- Chapter 3 contains parts of [2] and [3]
- Chapter 4 contains parts of [6] and [14]
- Chapter 5 contains parts of [8] and [9]
- Chapter 6 contains parts of [1] and [15]
- Chapter 7 contains parts of [14]



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Science is made up of so many things that appear obvious after they are explained.

- Frank Herbert in *Dune*

We are at the very beginning of time for the human race. It is not unreasonable that we grapple with problems. But there are tens of thousands of years in the future. Our responsibility is to do what we can, learn what we can, improve the solutions, and pass them on.

- Richard P. Feynman

You want a reason? How's about "Because"?

- Joshua Homme in *Turnin' on the Screw*

